NSN 5962-01-381-8265

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View Online at https://aerobasegroup.com/nsn/5962-01-381-8265

Maximum Power Dissipation Rating:

1.2 watts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Used on (07187) 8515143-910

Features Provided:

Programmed and tested to mil-std-883

Inclosure Configuration:

Leaded chip carrier

Output Logic Form:

Bipolar metal-oxide semiconductor

Input Circuit Pattern:

16 input

Case Outline Source And Designator:

C-2 mil-m-38510

Terminal Surface Treatment:

Solder

Product Name:

Programmed/16-input 8-output registered and-or gate array

Voltage Rating And Type Per Characteristic:

4.5 volts applied and 5.5 volts applied

Memory Device Type:

Pal

Hybrid Technology Type:

Monolithic

Test Data Document:

81349-mil-m-38510 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). And 07187-tt8518595-101 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

20 printed circuit

Specification Data:

67268-5962-85155182a government standard

Departure From Cited Document:

Modified by programming

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

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